NSN 5961-01-203-5802

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-203-5802 **Inclosure Material:** Metal **Overall Length:** 0.812 inches **End Application:** Memory s. Land class as; supply class aoe; ticonderoga class cg (47); forrestal class cv; arleigh burke class ddg; tarawa class lha; wasp class lhd; nimitz class cvn; landing system automatic carrier, dual channel **Mounting Facility Quantity:** 1 **Mounting Method:** Threaded stud **Overall Width Across Flats:** 0.688 inches **Thread Size:** 0.250 inches **Criticality Code Justification:** Feat **Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** 1200.0 reverse voltage, dc **Current Rating Per Characteristic:** 3.00 milliamperes forward current, average peak **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Special Features:** Weapon system essential; junction pattern arrangement: pn **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 tab, solder lug and 1 threaded stud Shelf Life: N/a **Unit Of Measure: Demilitarization:**

No

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